



P01 Series

SENSITIVE

0.8A SCRs

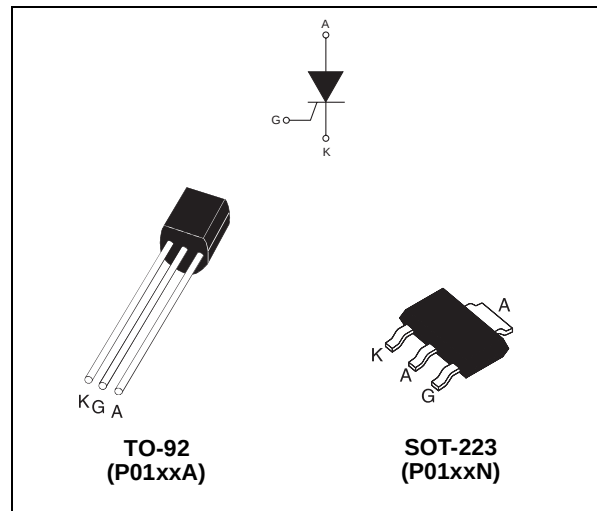
MAIN FEATURES:

Symbol	Value	Unit
$I_{T(RMS)}$	0.8	A
V_{DRM}/V_{RRM}	400 and 600	V
I_{GT}	5 to 200	μA

DESCRIPTION

Thanks to highly sensitive triggering levels, the P01 SCR series is suitable for all applications where available gate current is limited, such as ground fault circuit interruptors, pilot circuits in solid state relays, stand-by mode power supplies, smoke and alarm detectors.

Available in through-hole or surface mount packages, the voltage capability of this series has been upgraded since its introduction, to reach 600 V.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	TO-92	$T_I = 55^{\circ}C$	0.8	A
		SOT-223	$T_{amb} = 70^{\circ}C$		
$I_{T(AV)}$	Average on-state current (180° conduction angle)	TO-92	$T_I = 55^{\circ}C$	0.5	A
		SOT-223	$T_{amb} = 70^{\circ}C$		
I_{TSM}	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	$T_j = 25^{\circ}C$	8	A
		$t_p = 10 \text{ ms}$		7	
$I^2 t$	$I^2 t$ Value for fusing	$t_p = 10 \text{ ms}$	$T_j = 25^{\circ}C$	0.24	$A^2 s$
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \leq 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^{\circ}C$	50	$A/\mu s$
I_{GM}	Peak gate current	$t_p = 20 \mu s$	$T_j = 125^{\circ}C$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^{\circ}C$	0.1	W
T_{stg} T_j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	$^{\circ}C$

P01 Series

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified)

Symbol	Test Conditions			P01xx			Unit
				02	11	18	
I _{GT}	V _D = 12 V R _L = 140 Ω		MIN.	-	4	0.5	μA
			MAX.	200	25	5	
V _{GT}			MAX.	0.8			V
V _{GD}	V _D = V _{DRM} R _L = 3.3 kΩ R _{GK} = 1 kΩ	T _j = 125°C	MIN.	0.1			V
V _{RG}	I _{RG} = 10 μA		MIN.	8			V
I _H	I _T = 50 mA R _{GK} = 1 kΩ		MAX.	5			mA
I _L	I _G = 1 mA R _{GK} = 1 kΩ		MAX.	6			mA
dV/dt	V _D = 67 % V _{DRM} R _{GK} = 1 kΩ	T _j = 125°C	MIN.	75	80	75	V/μs
V _{TM}	I _{TM} = 1.6 A t _p = 380 μs	T _j = 25°C	MAX.	1.95			V
V _{t0}	Threshold voltage	T _j = 125°C	MAX.	0.95			V
R _d	Dynamic resistance	T _j = 125°C	MAX.	600			mΩ
I _{DRM} I _{RDM}	V _{DRM} = V _{RRM} = 400 V R _{GK} = 1 kΩ	T _j = 25°C	MAX.	1			μA
	V _{DRM} = V _{RRM} = 600 V R _{GK} = 1 kΩ			10			μA
	V _{DRM} = V _{RRM} R _{GK} = 1 kΩ	T _j = 125°C	MAX.	100			μA

THERMAL RESISTANCES

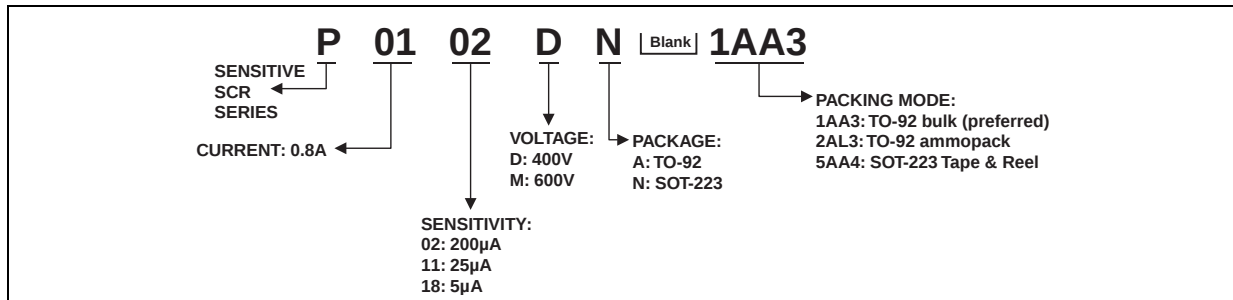
Symbol	Parameter		Value	Unit
R _{th(j-i)}	Junction to case (DC)	TO-92	80	°C/W
R _{th(j-t)}	Junction to tab (DC)	SOT-223	30	°C/W
R _{th(j-a)}	Junction to ambient	TO-92	150	
	S = 5 cm ²	SOT-223	60	

S = Copper surface under tab

PRODUCT SELECTOR

Part Number	Voltage		Sensitivity	Package
	400 V	600 V		
P0102DA	X		200 μA	TO-92
P0102DN	X		200 μA	SOT-223
P0102MA		X	200 μA	TO-92
P0102MN		X	200 μA	SOT-223
P0111DA	X		25 μA	TO-92
P0111DN	X		25 μA	SOT-223
P0111MA		X	25 μA	TO-92
P0111MN		X	25 μA	SOT-223
P0118DA	X		5 μA	TO-92
P0118DN	X		5 μA	SOT-223
P0118MA		X	5 μA	TO-92
P0118MN		X	5 μA	SOT-223

ORDERING INFORMATION



OTHER INFORMATION

Part Number	Marking	Weight	Base Quantity	Packing mode
P01xxyA 1AA3	P01xxyA	0.2 g	2500	Bulk
P01xxyA 2AL3	P01xxyA	0.2 g	2000	Ampack
P0102yN 5AA4	P2y	0.12 g	1000	Tape & reel
P0111yN 5AA4	P1y	0.12 g	1000	Tape & reel
P0118yN 5AA4	P8y	0.12 g	1000	Tape & reel

Note: xx = sensitivity, y = voltage

Fig. 1: Maximum average power dissipation versus average on-state current.

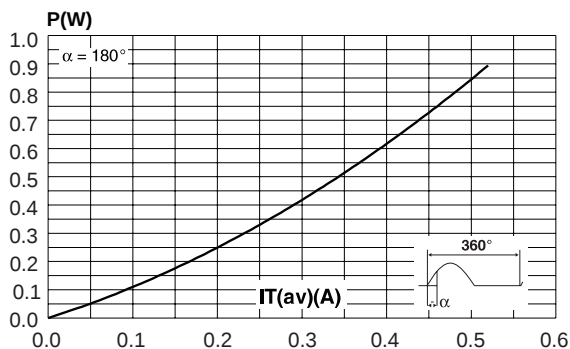


Fig. 2-2: Average and D.C. on-state current versus ambient temperature (device mounted on FR4 with recommended pad layout for SOT-223).

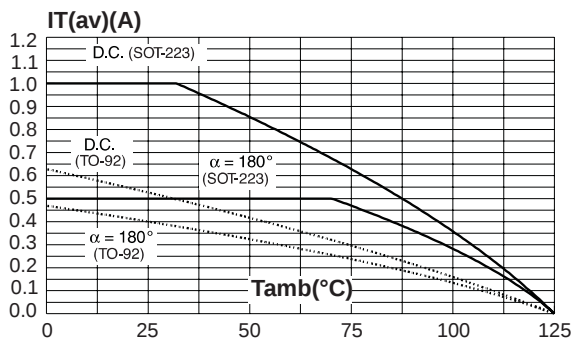


Fig. 2-1: Average and D.C. on-state current versus lead temperature.

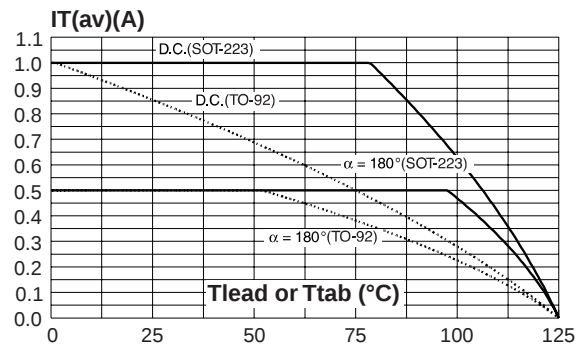


Fig. 3: Relative variation of thermal impedance junction to ambient versus pulse duration.

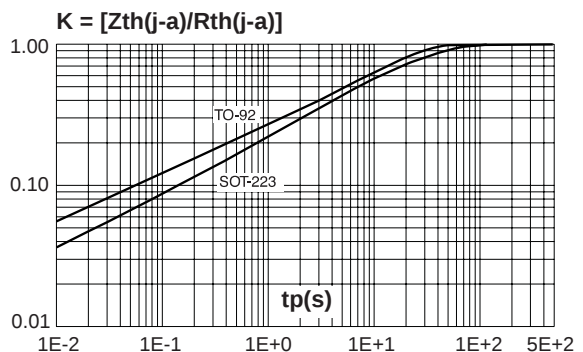


Fig. 4: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values).

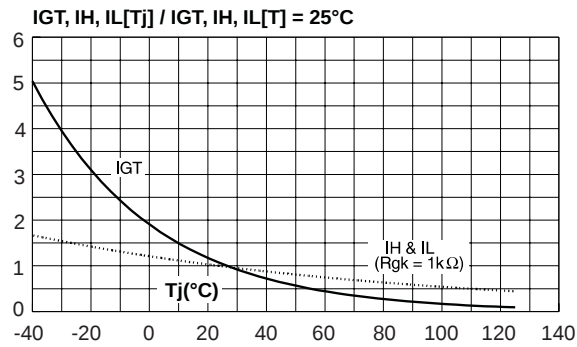


Fig. 6: Relative variation of dV/dt immunity versus gate-cathode resistance (typical values).

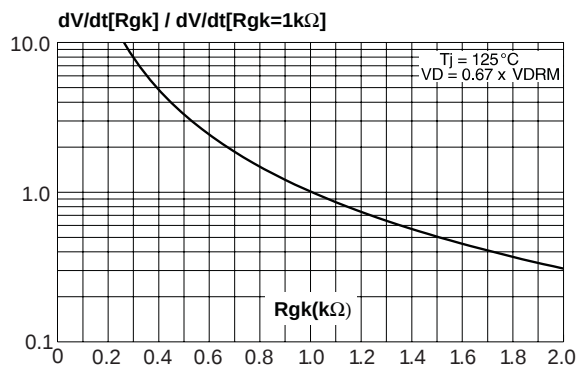


Fig. 8: Surge peak on-state current versus number of cycles.

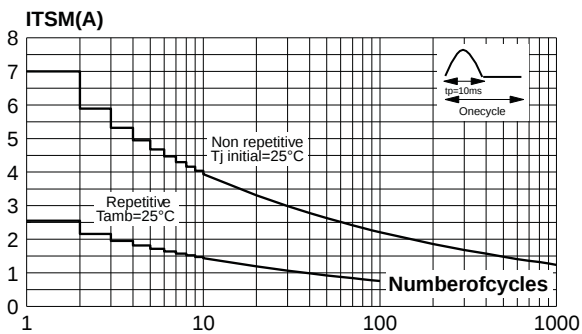


Fig. 5: Relative variation of holding current versus gate-cathode resistance (typical values).

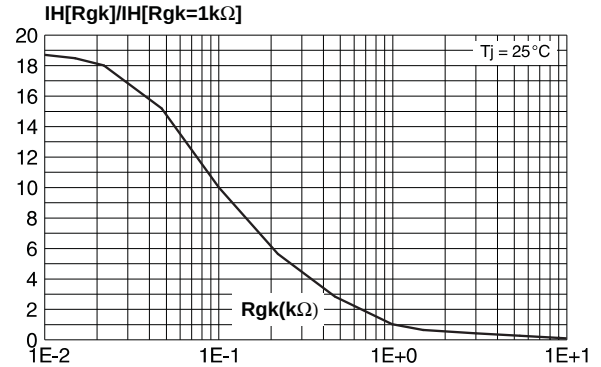


Fig. 7: Relative variation of dV/dt immunity versus gate-cathode capacitance (typical values).

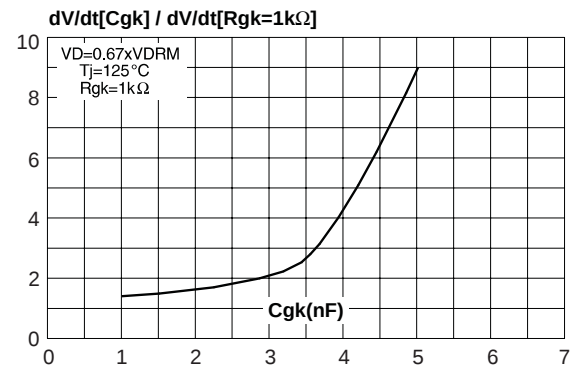


Fig. 9: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ ms}$, and corresponding value of I^2t .

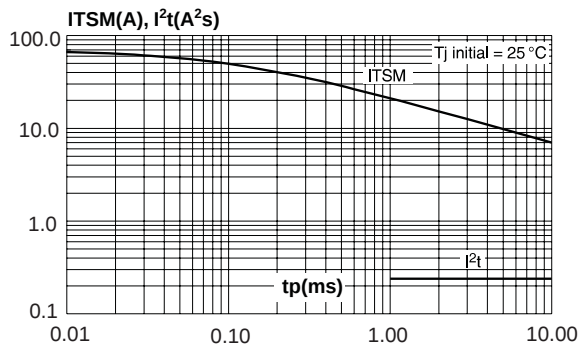


Fig. 10: On-state characteristics (maximum values).

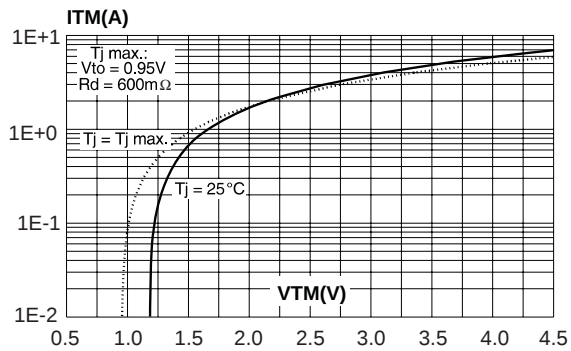
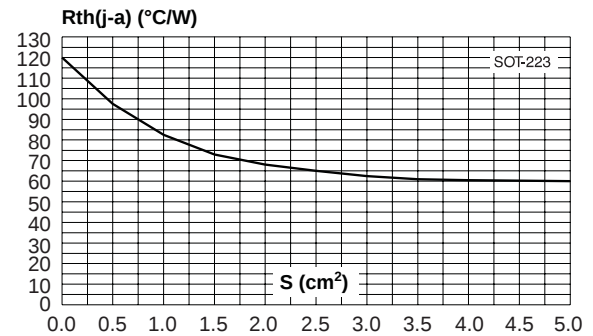
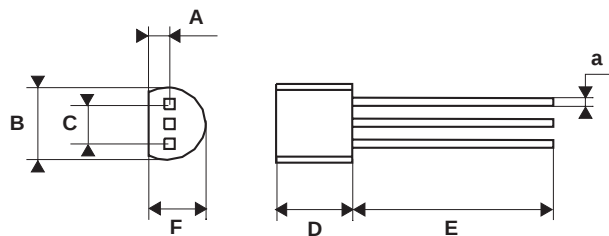


Fig. 11: SOT-223 Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35 μm).



PACKAGE MECHANICAL DATA

TO-92 (Plastic)



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		1.35			0.053	
B			4.70			0.185
C		2.54			0.100	
D	4.40			0.173		
E	12.70			0.500		
F			3.70			0.146
a			0.50			0.019

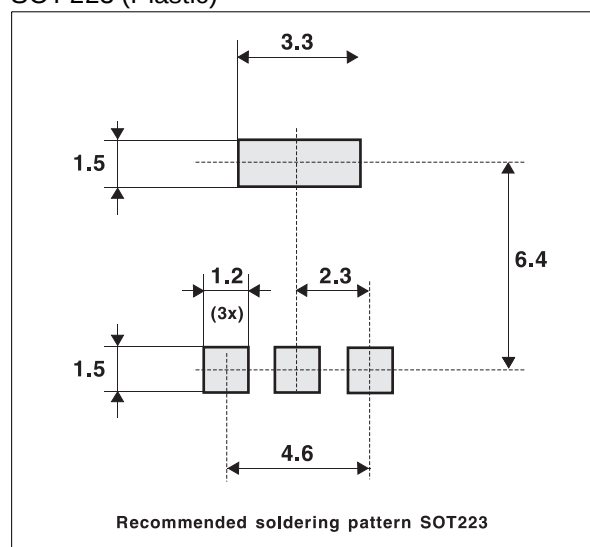
PACKAGE MECHANICAL DATA

SOT-223 (Plastic)

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.80			0.071
A1	0.02		0.1	0.0008		0.004
B	0.60	0.70	0.85	0.024	0.027	0.034
B1	2.90	3.00	3.15	0.114	0.118	0.124
c	0.24	0.26	0.35	0.009	0.010	0.014
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.3			0.090	
e1		4.6			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V	10° max					

FOOTPRINT DIMENSIONS (in millimeters)

SOT-223 (Plastic)



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2000 STMicroelectronics - Printed in Italy - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES
Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom

<http://www.st.com>

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru